MGBR60L100C **DIODE** 

# **DUAL MOS GATED BARRIER** RECTIFIER

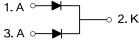
#### **DESCRIPTION**

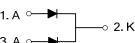
The UTC MGBR60L100C is a dual mos gated barrier rectifiers, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

#### **FEATURES**

- \* Low forward voltage drop
- \* High switching speed

#### **SYMBOL**

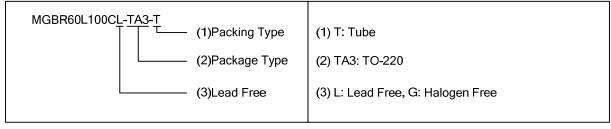




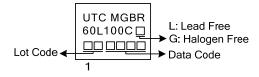
# **ORDERING INFORMATION**

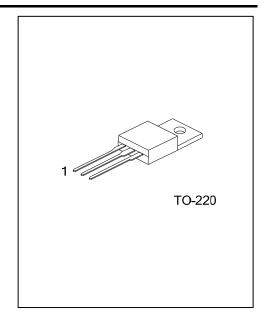
	Ordering Number		Package	Pin Assignment			Dooking	
Ī	Lead Free	Lead Free Halogen Free		1	2	3	Packing	
ſ	MGBR60L100CL-TA3-T	MGBR60L100CG-TA3-T	TO-220	Α	K	Α	Tube	

Note: Pin Assignment: A: Anode K: Cathode



## **MARKING**





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# ■ ABSOLUTE MAXIMUM RATINGS (PER LEG) (T<sub>A</sub>=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT
DC Blocking Voltage		$V_{RM}$	100	V
Working Peak Reverse Voltage	$V_{RWM}$	100	V	
Peak Repetitive Reverse Voltage		$V_{RRM}$	100	V
Average Rectified Output Current Per Device	Per Leg	l <sub>o</sub>	30	Α
verage Reclined Output Current Per Device	Total		60	Α
Non-Repetitive Peak Forward Surge Current 8 Half Sine-Wave Superimposed on Rated Load	n-Repetitive Peak Forward Surge Current 8.3ms Single f Sine-Wave Superimposed on Rated Load		280	Α
Operating Junction Temperature		TJ	-65~+150	°C
Storage Temperature		$T_{STG}$	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### **■ THERMAL DATA**

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	$\theta_{JA}$	62.5	°C/W	
Junction to Case	θις	2	°C/W	

## ■ ELECTRICAL CHARACTERISTICS (PER LEG) (T<sub>A</sub> =25°C unless otherwise specified.)

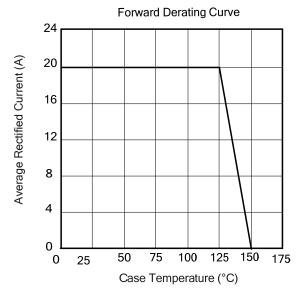
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I <sub>R</sub> =0.50mA	100			V
Forward Voltage Drop	VEM	I <sub>F</sub> =30A, T <sub>J</sub> =25°C			0.79	V
		I <sub>F</sub> =30A, T <sub>J</sub> =125°C			0.74	V
eakage Current (Note 1)	I DM	V <sub>R</sub> =100V, T <sub>J</sub> =25°C			200	μΑ
		V <sub>R</sub> =100V, T <sub>.I</sub> =125°C			20	mA

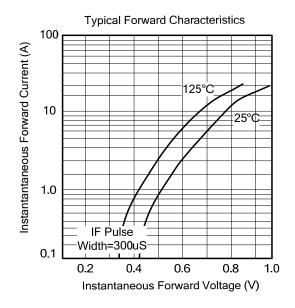
Notes: 1. Short duration pulse test used to minimize self-heating effect.

<sup>2.</sup> Thermal resistance junction to case mounted on heatsink.

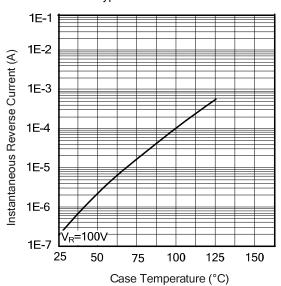
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## **■ TYPICAL CHARACTERISTICS**









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